



查询SI4719CY供应商

捷多邦，专业PCB打样工厂，24小时加急出货

Si4719CY

Vishay Siliconix

## Battery Disconnect Switch

### FEATURES

- Solution for Bi-Directional Blocking Bi-Directional Conduction Switch
- 6- to 30-V Operation
- Ground Referenced Logic Level Inputs
- Integrated Low  $r_{DS(on)}$  MOSFET
- Level-Shifted Gate Drive with Internal MOSFET

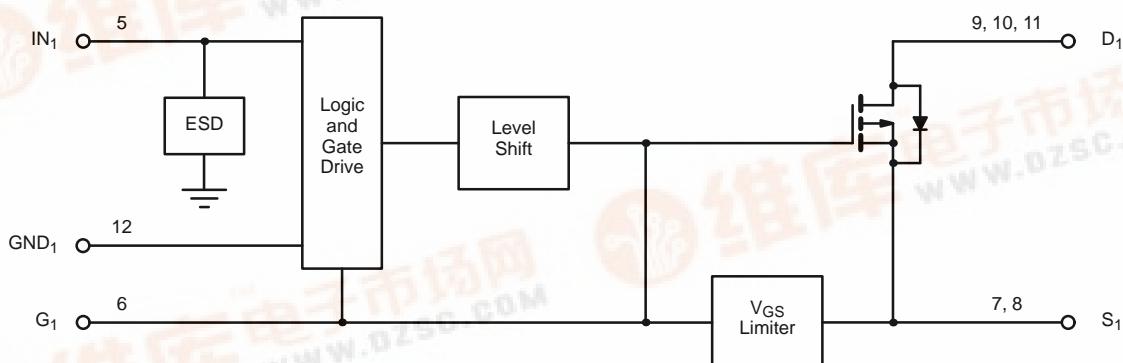
- Two Independent Inputs
- Includes Precision Voltage Circuitry
- Ultra Low Power Consumption in Off State (Leakage Current Only)
- Logic Supply Voltage is Not Required

### DESCRIPTION

The Si4719CY is two level-shifted p-channel MOSFETs. Operating together, these MOSFETs can be used as a reverse blocking switch for battery disconnect applications. It is a solution for multiple battery technology designs or designs that require isolation from the power bus during charging.

The Si4719CY is available in a 16-pin SOIC package and is rated for the commercial temperature range of  $-25$  to  $85^{\circ}\text{C}$ .

### FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION



## ABSOLUTE MAXIMUM RATINGS

Voltage Referenced to GND	
$V_S, V_D^a$	-0.3 V to 32 V
$V_{SD}$	-0.3 V to 30 V
$V_{IN1}, V_{IN2}$	-0.3 V to 15 V
$V_{GS}$	20 V
Storage Temperature	-55 to 150°C

Power Dissipation <sup>b</sup>	(t = 10 sec) .....	2.4 W
	(t = steady state) .....	1.5 W

### Notes

- a.  $V_{SD} \leq 30$  V<sub>DC</sub>
- b. Device mounted with all leads soldered to 1" x 1" FR4 with laminated copper PC board.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

## RECOMMENDED OPERATING RANGE

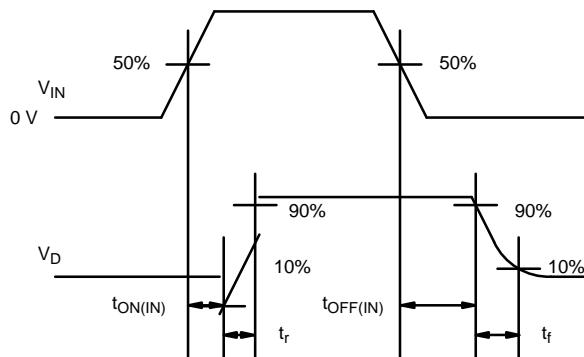
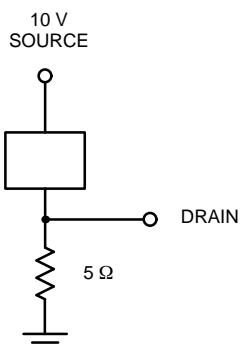
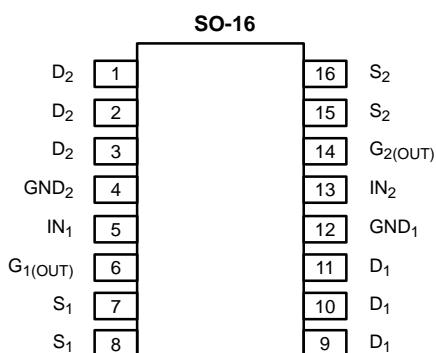
$V_S, V_D$	6 V to 30 V	Operating Temperature Range .....	-25 to 85°C
$V_{IN1}, V_{IN2}$	0 V to 13.2 V	Junction Temperature .....	-25 to 150°C
$I_{DS}$	0 A to 6 A		

## SPECIFICATIONS

Parameter	Symbol	Specific Test Conditions	Limits				Unit
			Temp <sup>a</sup>	Min <sup>b</sup>	Typ <sup>c</sup>	Max <sup>b</sup>	
On-Resistance	$r_{DS}$	$V_S = 10$ V, $I_D = 1$ A, $V_{IN} = H$	Room		0.028	0.040	Ω
Leakage Current	$I_{DS(off)}$	$V_{DS} = 10$ V	Room			1	
Power Consumption	$I_S$ GND <sub>(off)</sub>	$V_S = 21$ V	Room			1	μA
	$I_S$ GND <sub>(on)</sub>		Room		1.0	10	
Input Voltage Low	$V_{INL}$	$V_S = 10$ V and $V_S = 21$ V	Full			3.3	V
Input Voltage High	$V_{INH}$		Full	4.5			
Input Current	$I_{INH}$	$V_{IN} = 5.0$ V	Room		25	50	μA
Turn-On Delay	$t_{ON(IN)}$	$V_S = 10$ V, $R_L = 5$ Ω, Test Circuit 1	Room	2.2	2.9	10	μs
Turn-Off Delay	$t_{OFF(IN)}$		Room		1.15	2	
Break-Before-Make <sup>d</sup>	$t_{BBM}$		Room		1.15		
Rise Time	$t_{RISE}$		Room		0,73	1.4	
Fall Time	$t_{FALL}$		Room		24	50	ns
Voltage Across Pin 6 and 7	$V_{GS}$	$V_S = 30$ V	Room		10.2	18	V
Forward Diode	$V_{SD}$	$I_D = -1$ A	Room			1.1	

### Notes

- a. Room = 25°C, Full = as determined by the operating temperature suffix.
- b. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum.
- c. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.
- d. Guaranteed by design, not subject to production testing.

**TIMING DIAGRAMS**

**TEST CIRCUIT 1**
**PIN CONFIGURATION**


Top View

Order Number: Si4719CY

TRUTH TABLE			
$V_{IN1}$	$V_{IN2}$	Switch 1	Switch 2
0	0	Off	Off
0	1	Off	On
1	0	On	Off
1	1	On	On

**PIN DESCRIPTION**

Pin Number	Symbol	Description
1, 2, 3	D <sub>2</sub>	Drain connection for MOSFET-2.
4, 12	GND	Ground
5	IN <sub>1</sub>	Logic input, IN <sub>1</sub> . High level turns on the switch.
6	G <sub>1</sub> (OUT)	Gate output to MOSFET-1.
7, 8	S <sub>1</sub>	Source connection for MOSFET-1
9, 10, 11	D <sub>1</sub>	Drain connection for MOSFET-1.
13	IN <sub>2</sub>	Logic input, IN <sub>2</sub> . High level turns on the switch.
14	G <sub>2</sub> (OUT)	Gate output to MOSFET-2.
15, 16	S <sub>2</sub>	Source connection for MOSFET-2.

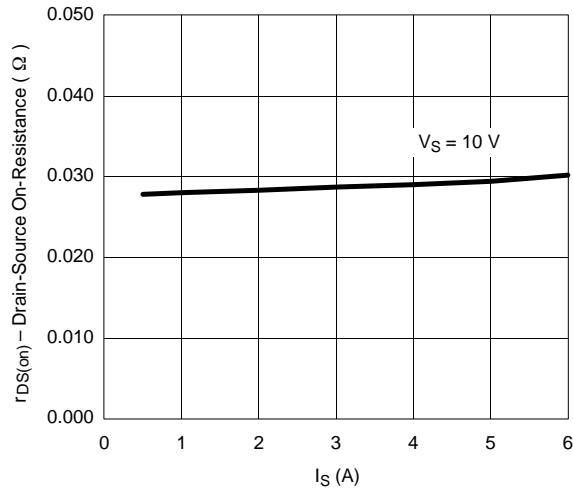
# Si4719CY

## Vishay Siliconix

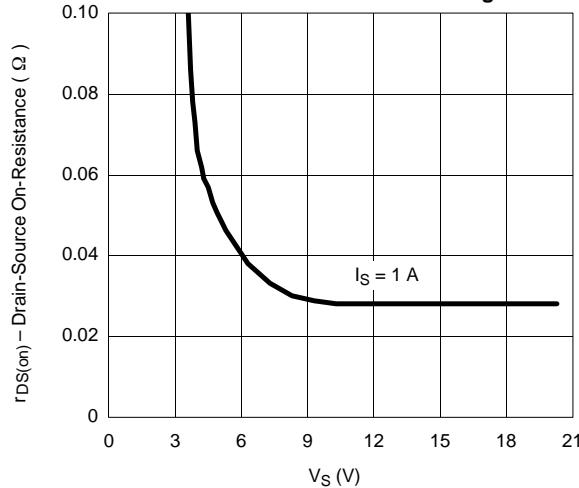


### TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

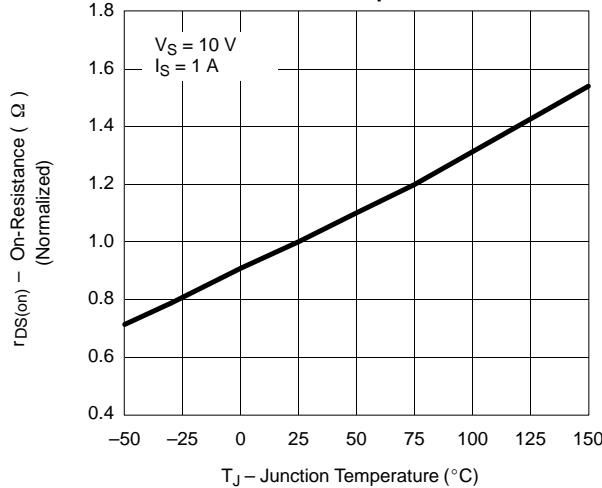
On-Resistance vs. Drain Current



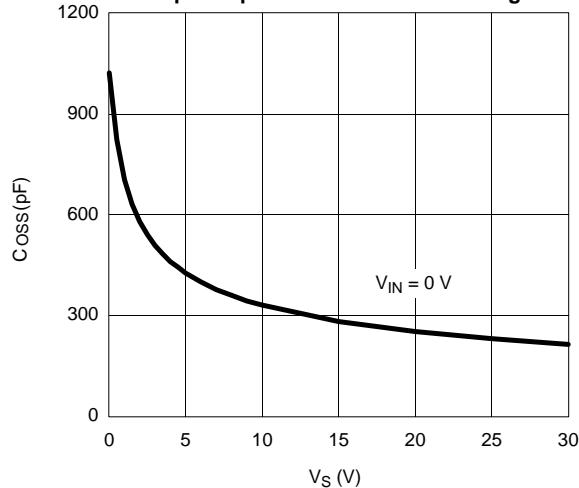
On-Resistance vs. Source Voltage



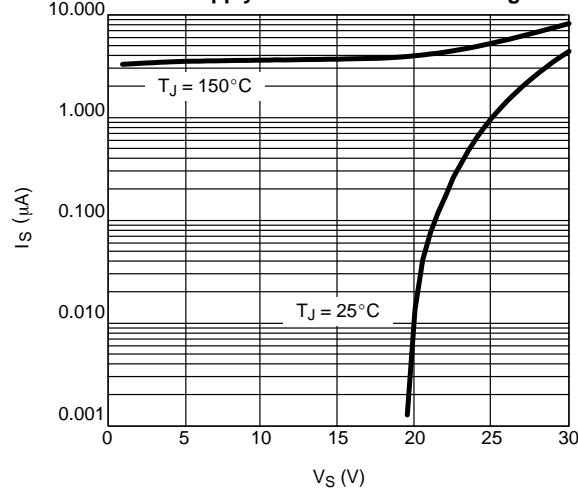
Normalized On-Resistance vs. Junction Temperature



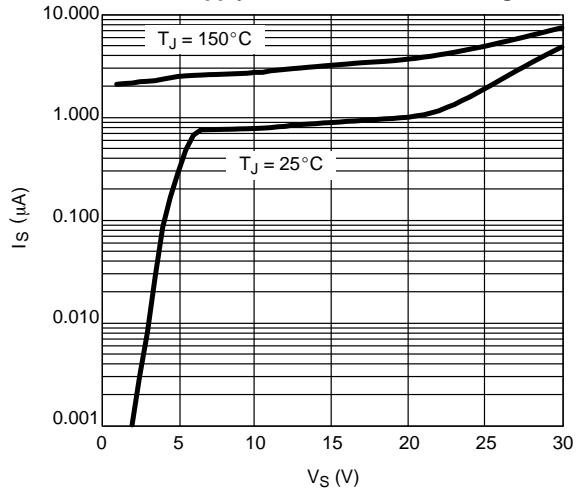
Output Capacitance vs. Source Voltage

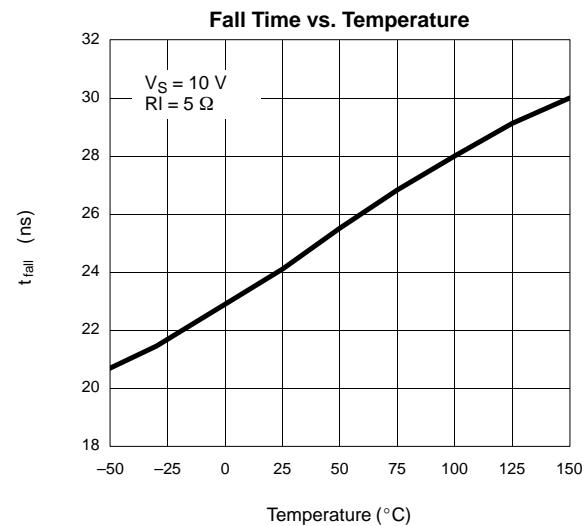
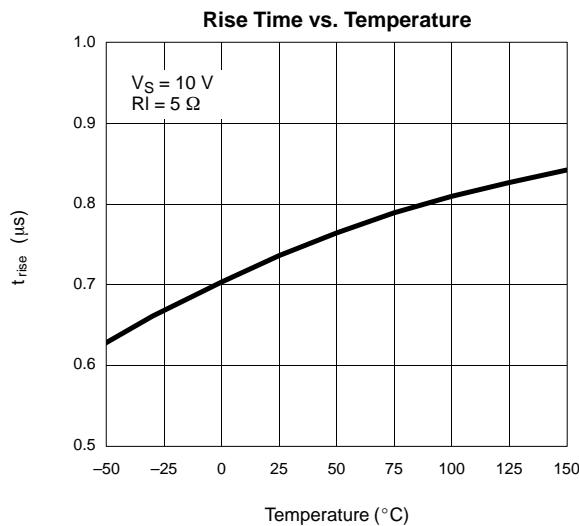
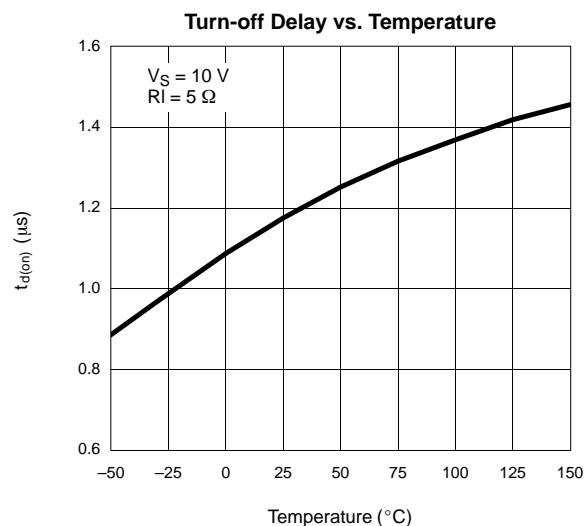
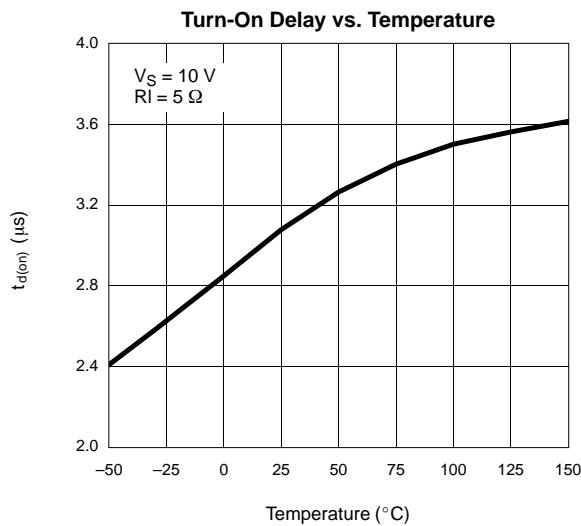
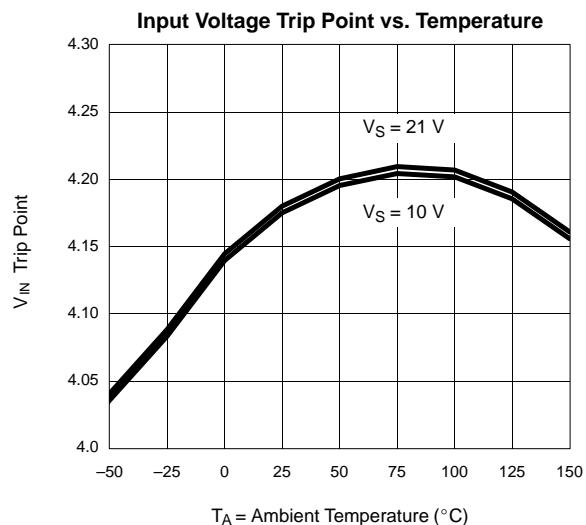
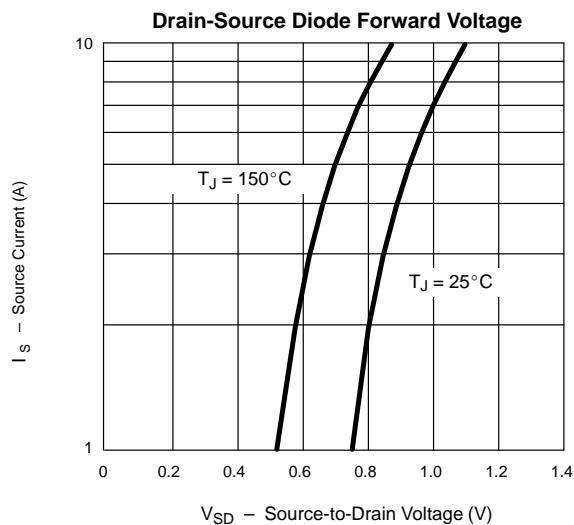


Off-Supply Current vs. Source Voltage



On-Supply Current vs. Source Voltage



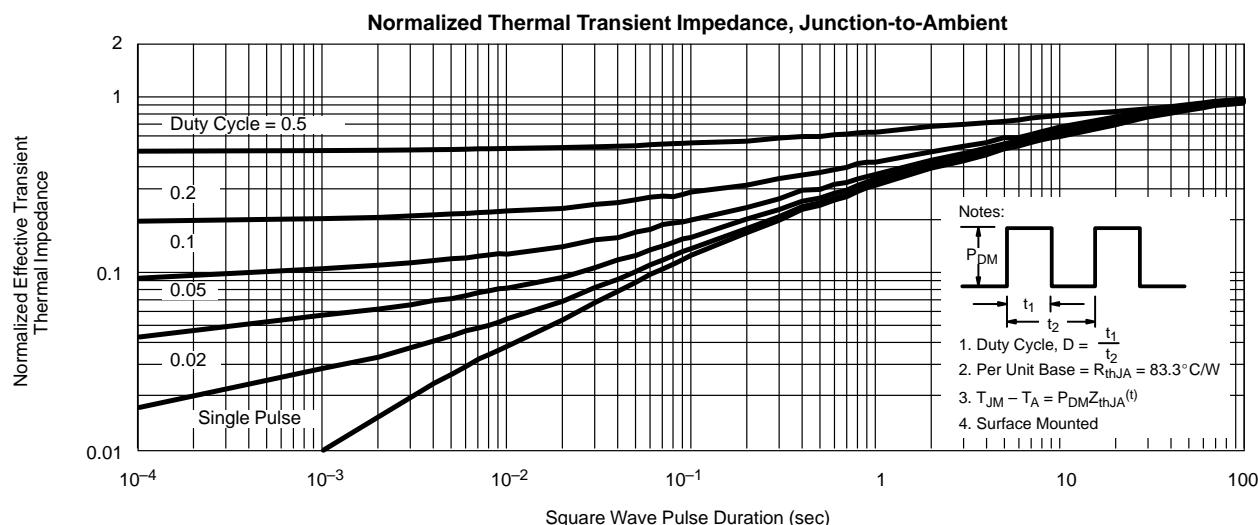
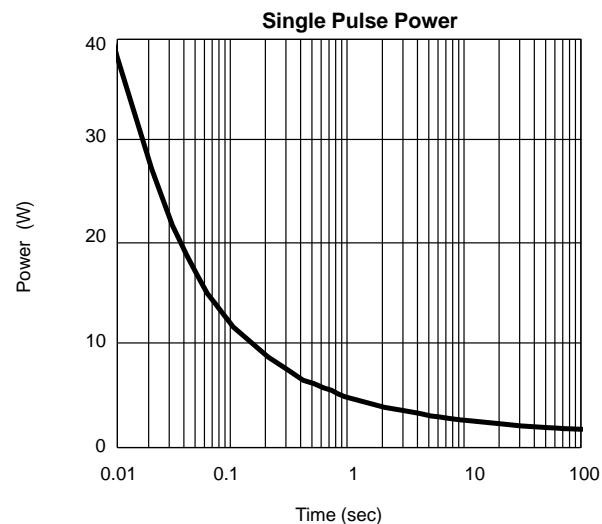
**TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)**


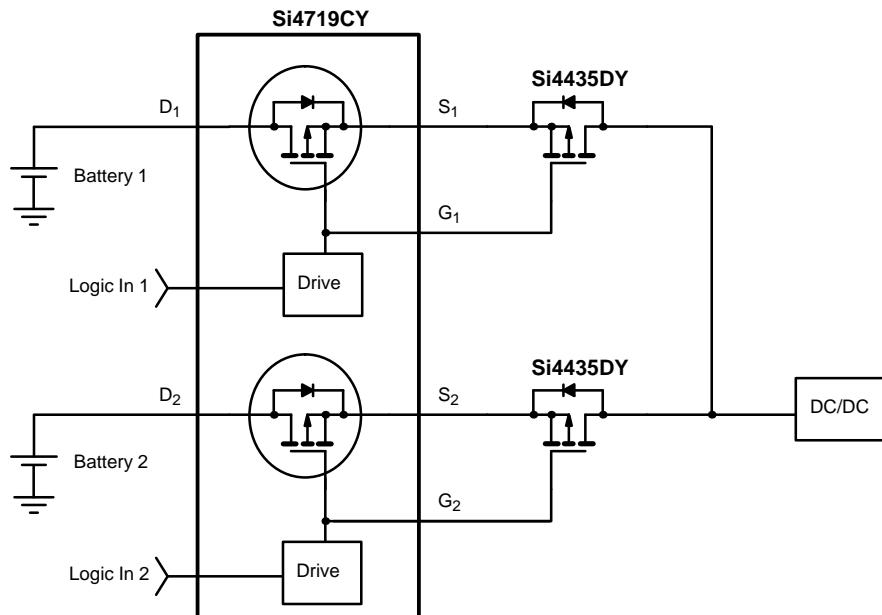
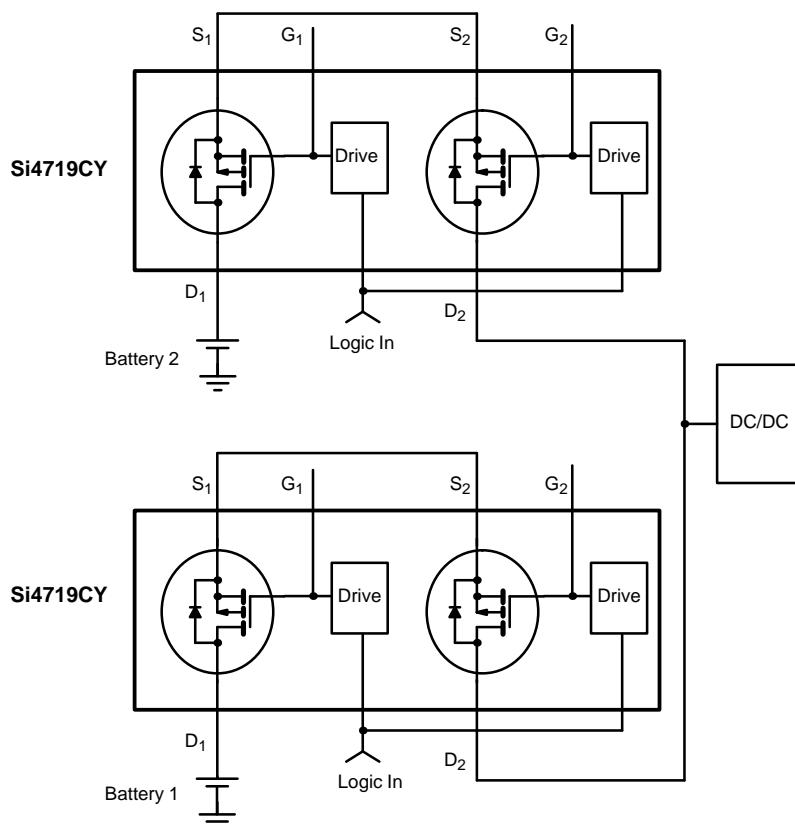
**Si4719CY**

Vishay Siliconix



**TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)**



**APPLICATION DRAWINGS**

**FIGURE 1**

**FIGURE 2**

# Si4719CY

Vishay Siliconix



## APPLICATION DRAWINGS

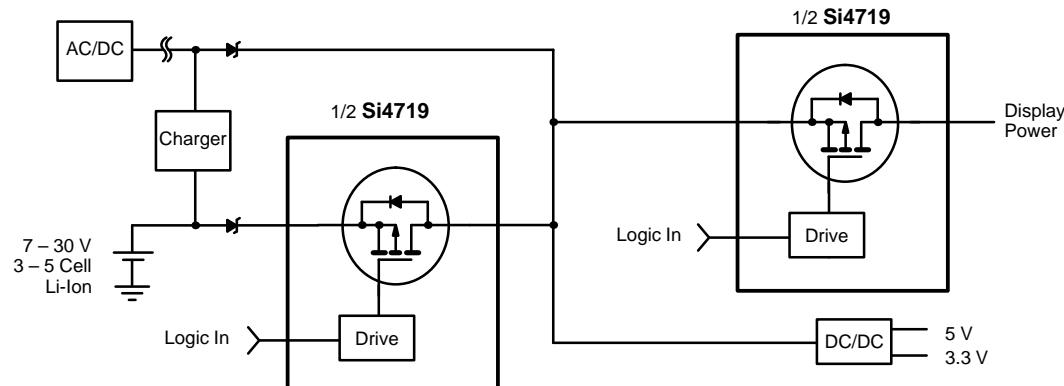


FIGURE 3: Low-Cost Laptop PC

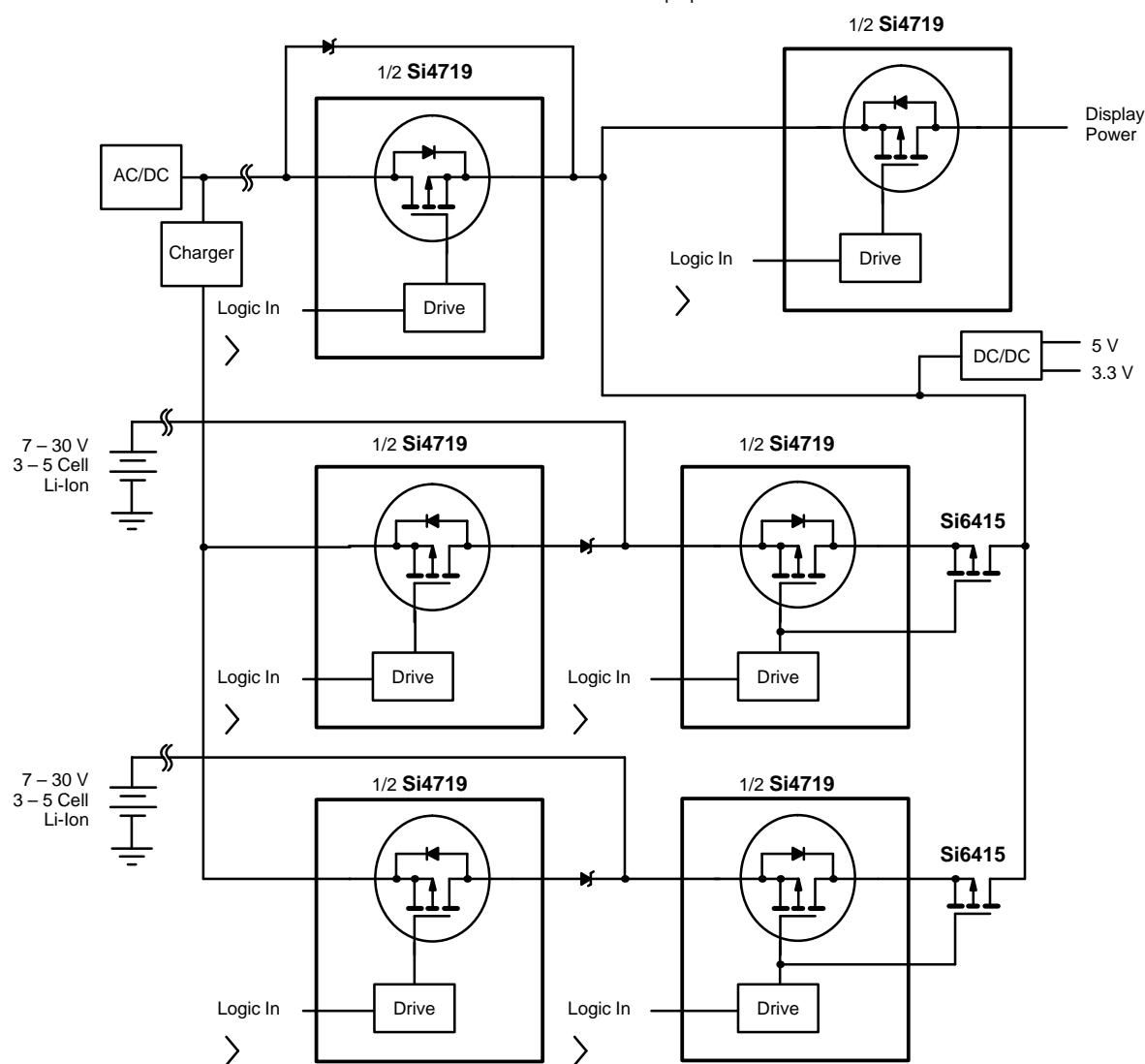


FIGURE 4: High-Performance Laptop PC